CLAIMS

What is claimed is:

1	1.	A magnetic head coil structure, comprising:
2		an insulating layer;
3		a photoresist layer deposited on the insulating layer;
4		a silicon dielectric layer deposited on the photoresist layer, the silicon dielectric
5	layer l	naving at least one channel formed therein;
6		a conductive material formed in the at least one channel to define a coil structure
		-
1	2.	The coil structure as recited in claim 1, wherein the insulating layer includes
2		Al_2O_3 .
1	3.	The coil structure as recited in claim 1, wherein the conductive seed layer
2		includes Cu.
1	4.	The coil structure as recited in claim 1, wherein the conductive material includes
2		Cu.
1	5.	The coil structure as recited in claim 1, wherein a grain size of the conductive
2		material is less than half of a smallest dimension of the at least one channel.

- 1 6. The coil structure as recited in claim 1, wherein a resistivity of the conductive seed layer is less than or equal to 8.3 micro-ohm/cm.
- The coil structure as recited in claim 1, wherein the silicon dielectric layer includes SiO₂.
- 1 8. The coil structure as recited in claim 1, wherein the at least one channel includes a slope greater than one (1).
- The coil structure as recited in claim 1, wherein the slope of the at least one channel facilitates depositing of the conductive seed layer and the conductive material.
- 1 10. The coil structure as recited in claim 1, wherein an aspect ratio of the at least one channel is at least 7.
- 1 11. The coil structure as recited in claim 1, wherein the channels are formed by
 2 masking, wherein the masking includes depositing another photoresist layer.
- 1 12. The coil structure as recited in claim 1, wherein at least a portion of the silicon dielectric layer has been removed.

- The coil structure as recited in claim 12, wherein the silicon dielectric layer has 1 13. been removed by chemical-mechanical polishing (CMP). 2 The coil structure as recited in claim 1, and further comprising an adhesion 1 14. promoter layer between the silicon dielectric layer and the photoresist layer. 2 The coil structure as recited in claim 1, wherein the conductive seed layer 1 15. 2 includes a magnetic material. The coil structure as recited in claim 1, wherein the conductive material includes a 1 16. 2 magnetic material. 1 17. The coil structure as recited in claim 16, wherein the magnetic material is selected from the group consisting of NiFe, CoFe, and CoNiFe. 2 The coil structure as recited in claim 1, wherein the coil structure includes a P2 1 18. 2 pole tip structure. A disk drive system, comprising: 1 19. 2 a magnetic recording disk;
- a magnetic head including a coil structure as recited in claim 1;
- an actuator for moving the magnetic head across the magnetic recording disk so
- 5 the magnetic head may access different regions of the magnetic recording disk; and

1 A magnetic head coil structure manufactured utilizing a process, comprising: 20. 2 depositing an insulating layer; 3 depositing a photoresist layer on the insulating layer; depositing a silicon dielectric layer on the photoresist layer; 4 5 masking the silicon dielectric layer; 6 etching at least one channel in the photoresist layer and the silicon dielectric 7 layer; depositing a conductive seed layer in the at least one channel; and 8 9 filling the at least one channel with a conductive material to define a coil 10 structure. A disk drive system, comprising: 1 21. 2 a magnetic recording disk; 3 a magnetic head including a coil structure as recited in claim 20; an actuator for moving the magnetic head across the magnetic recording disk so 4 5 the magnetic head may access different regions of the magnetic recording disk; and 6 a controller electrically coupled to the magnetic head. A magnetic head coil structure manufactured utilizing a process, comprising: 1 22. 2 depositing a conductive layer; 3 depositing a photoresist layer on the conductive layer;

a controller electrically coupled to the magnetic head.

6

- 4 depositing a silicon dielectric layer on the photoresist layer;
- 5 masking the silicon dielectric layer;
- 6 etching at least one channel in the photoresist layer and the silicon dielectric
- 7 layer;
- 8 filling the at least one channel partially with a conductive material; and
- 9 removing the photoresist layer, the silicon dielectric layer, and the conductive
- layer to define the magnetic head coil structure.